TO-92 Plastic-Encapsulate Transistors

AV4401 TRANSISTOR（NPN）

TO—92



1.EMILTTER

2.BASE

3. COLLECTOR

1 2 3

FEATURES

Power dissipation

P_{CM} : 0.625 W (Tamb=25℃)

Collector current

$I_{CM:}$ 0.6 A

Collector-base voltage

$V_{(BR)CBO}$: 60 V

Operating and storage junction temperature range

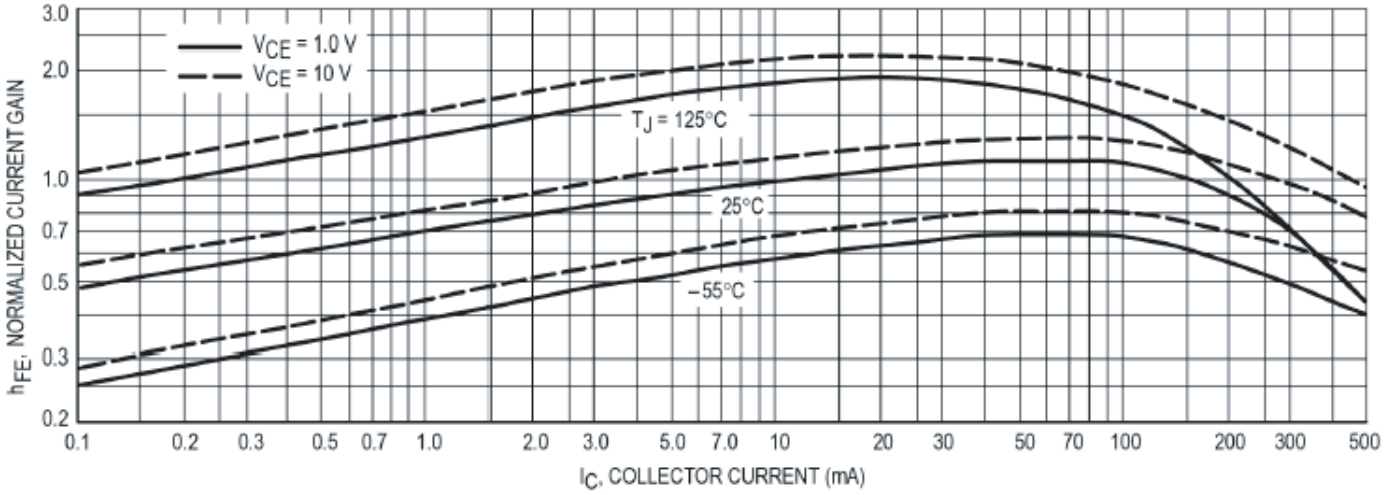
T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS（Tamb=25℃ unless otherwise specified）

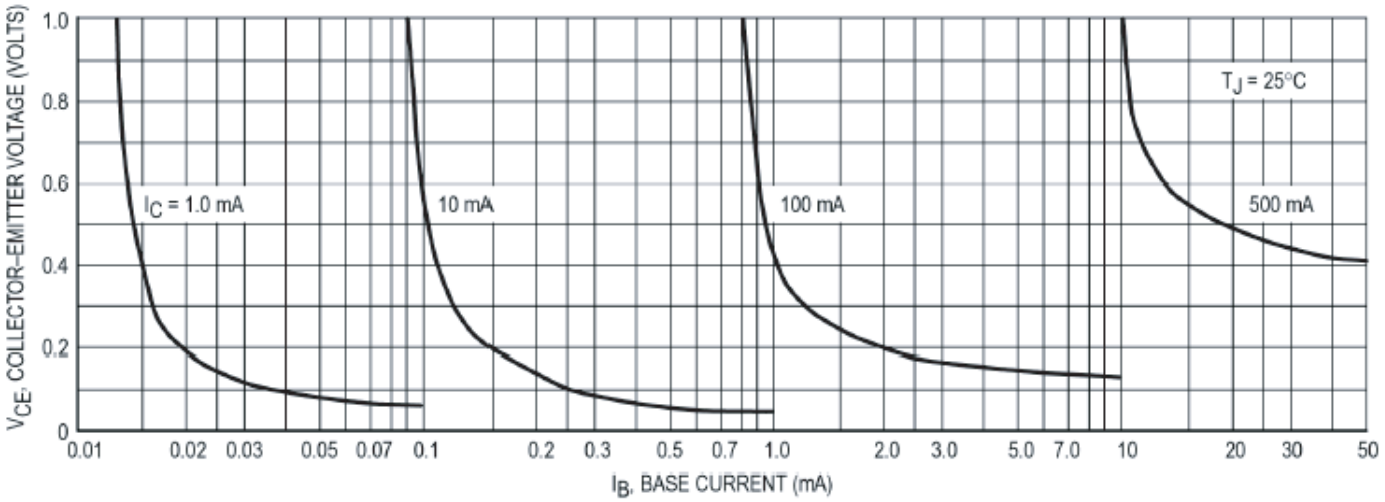
Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C=100μA, I_E=0	60		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C= 1mA, I_B=0	40		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=100μA, I_C=0	6		V
Collector cut-off current	I_{CBO}	V_{CB}=50 V, I_E=0		0.1	μA
Collector cut-off current	I_{CEO}	V_{CE}=35 V, I_B=0		0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}=5V, I_C=0		0.1	μA
DC current gain	$h_{FE\ (1)}$	V_{CE}=1 V, I_C= 150mA	100	300	
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=150 mA, I_B=15mA		0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	I_C= 150 mA, I_B=15mA		0.95	V
Transition frequency	f_T	V_{CE}= 10V, I_C= 20mA f = 100MHz	250		MHz

Copyright @vic Electronics Corp.

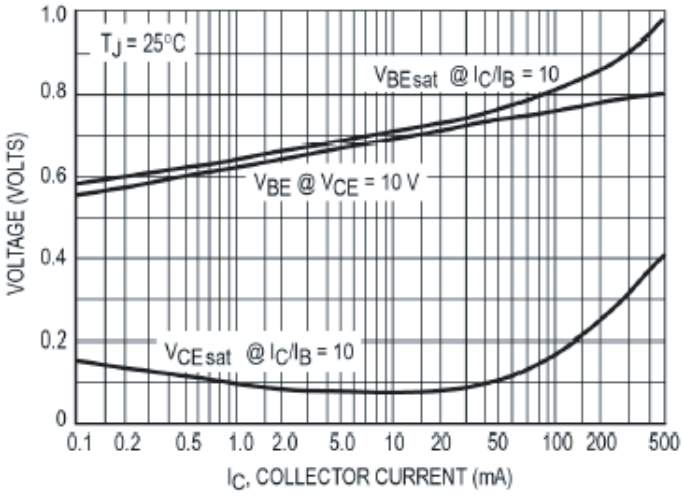
Typical Characteristics



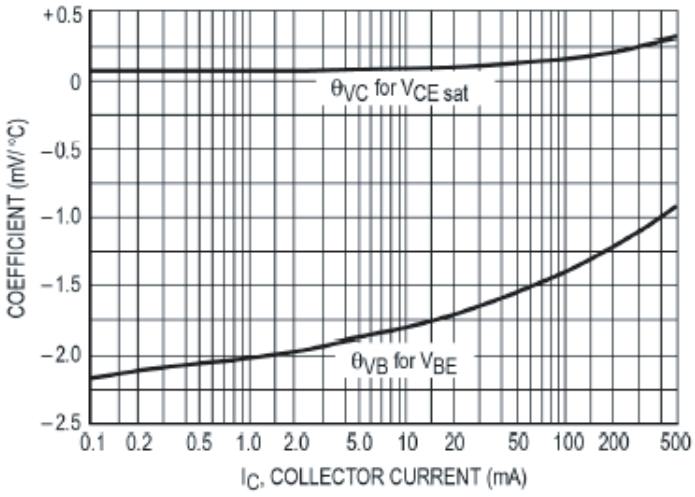
DC Current Gain



Collector Saturation Region

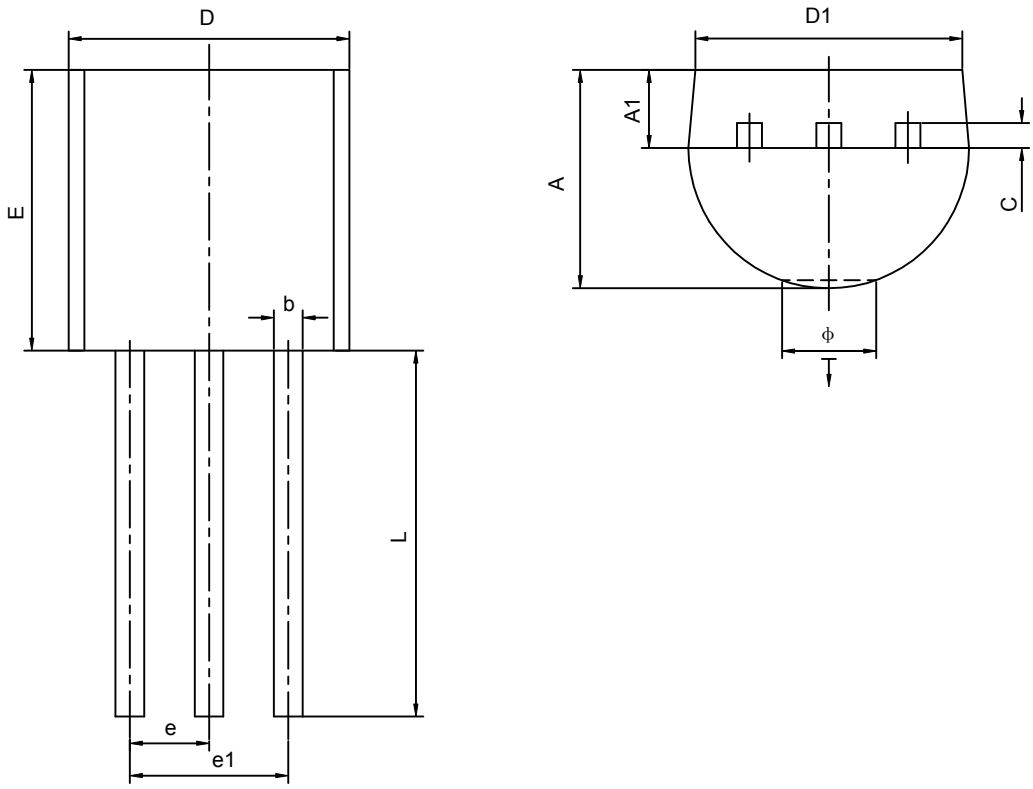


"On" Voltages



Temperature Coefficients

TO-92 PACKAGE OUTLINE DIMENSIONS



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	3.300	3.700	0.130	0.146
A1	1.100	1.400	0.043	0.055
b	0.380	0.550	0.015	0.022
c	0.360	0.510	0.014	0.020
D	4.400	4.700	0.173	0.185
D1	3.430		0.135	
E	4.300	4.700	0.169	0.185
e	1.270TYP		0.050TYP	
e1	2.440	2.640	0.096	0.104
L	14.100	14.500	0.555	0.571
Ö		1.600		0.063
⊤	0.000	0.380	0.000	0.015